Lecture 04: Small Signal Modeling

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Outline

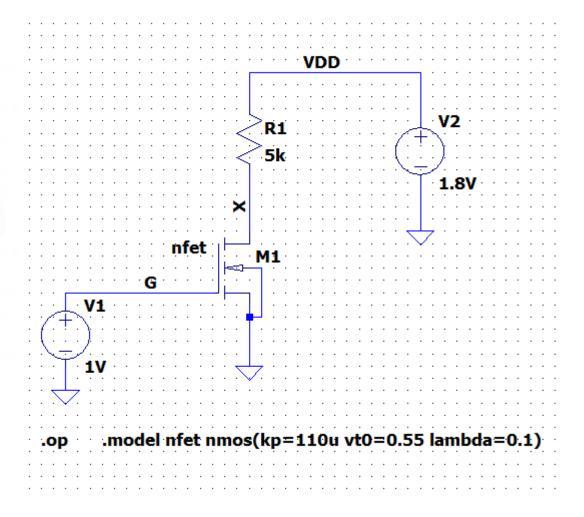
□ Introduction

☐ Signal Definitions

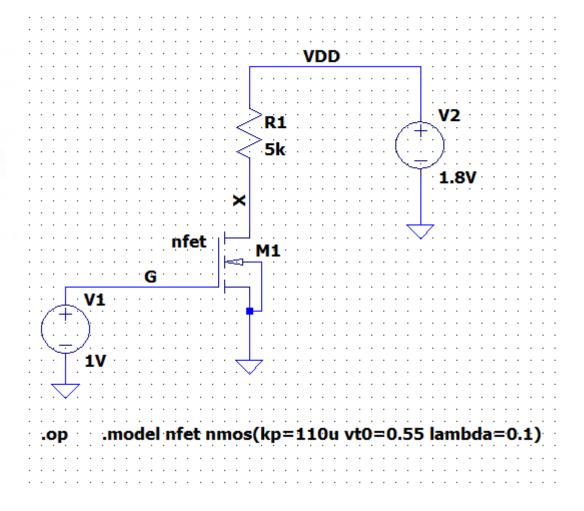
□Small-Signal Modeling

□ Conclusions

Introduction

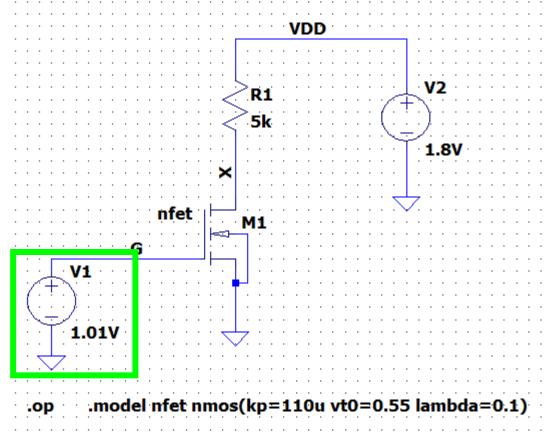


Introduction – Changing Values



Introduction – Changing Values

12= (193.97 m) (1 + 0.1 (1.8-5000 ln))



Introduction – Changing Values

$$lo = \frac{1}{2} \mu_{N}(0x \frac{N}{L} (V_{65} - V_{74}) \cdot (1 + \lambda V_{D5})$$

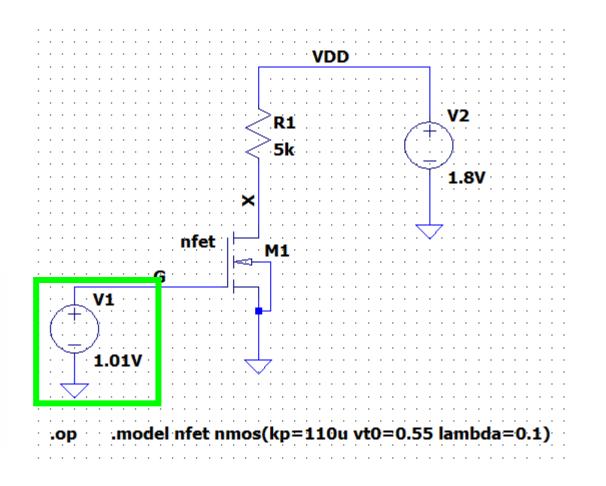
$$lo = (185.6 \, \mu) (1 + 0.1 (1.8 - 5000 \, lo))$$

$$lv = 200.4 \, \mu A$$

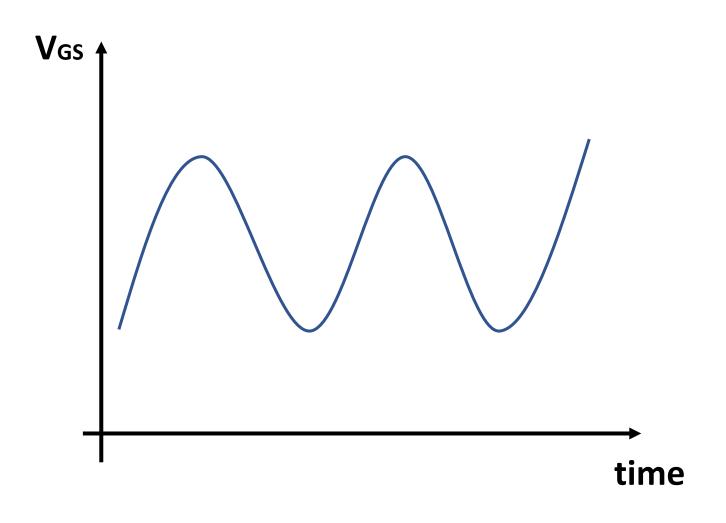
$$V_{652} = V_{65} + \Delta V_{65} ; \Delta V_{65} = 10 \, mV$$

$$lo = 208.65 \, \mu A \Rightarrow lo = lo + \Delta lo$$

$$\Delta lo = 8.25 \, \mu A$$

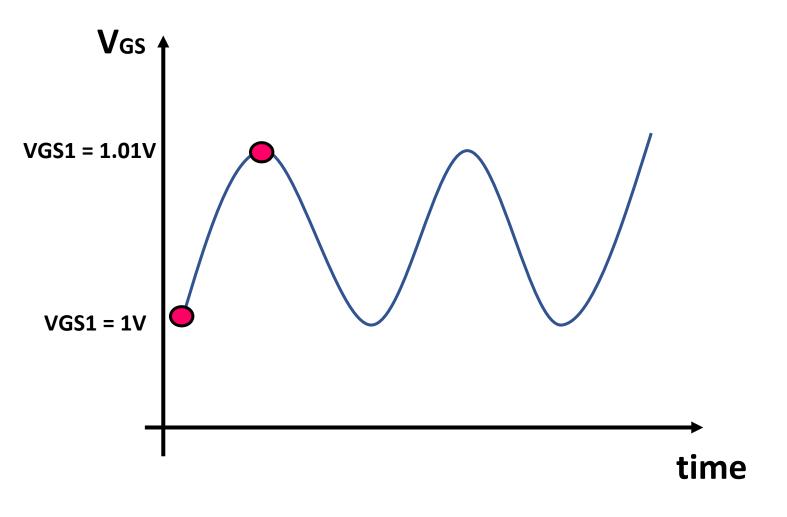


Signals



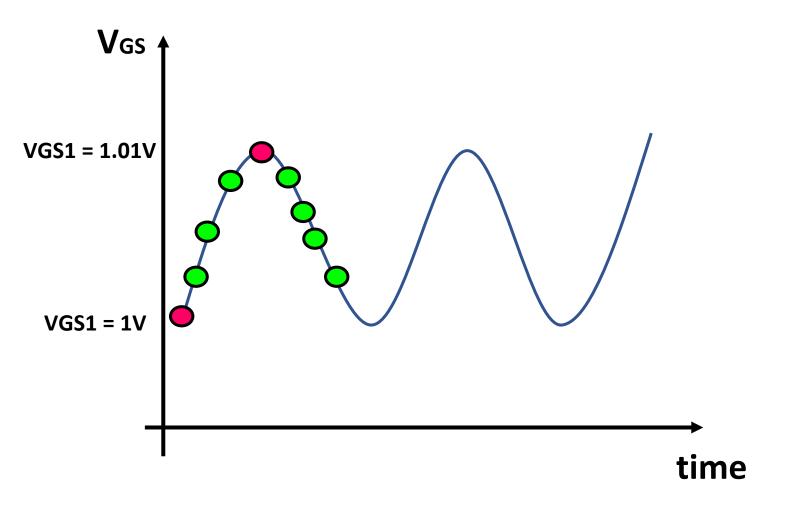
What if we put a signal?

Signals



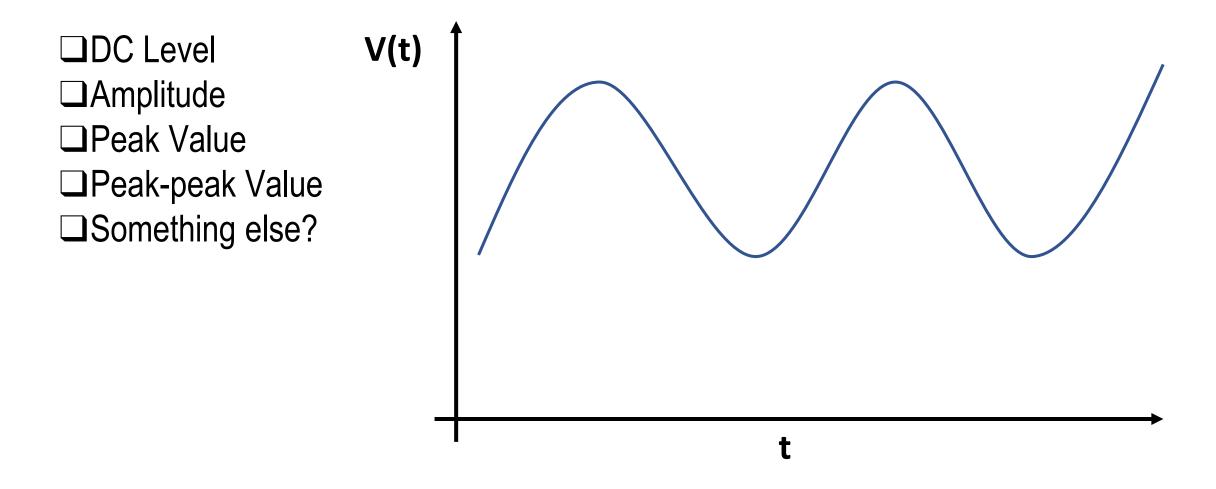
Think of a signal between the two previous values

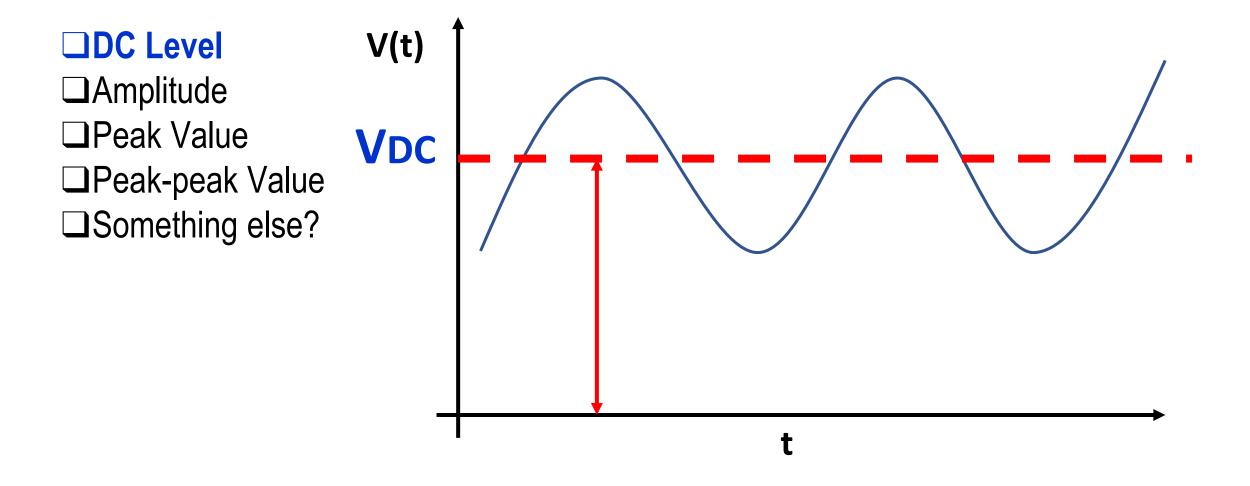
Signals

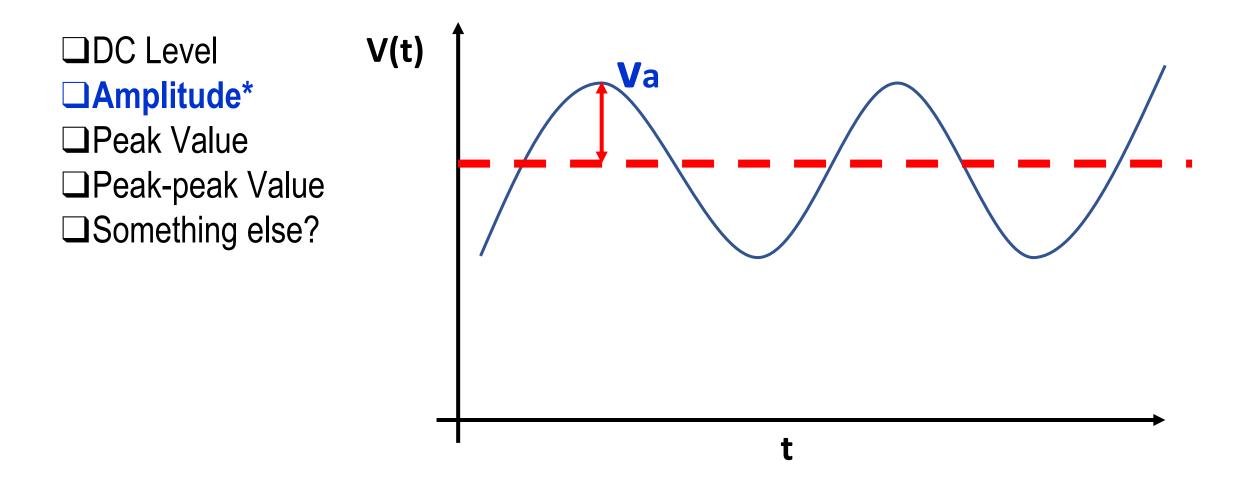


We need to solve for each point

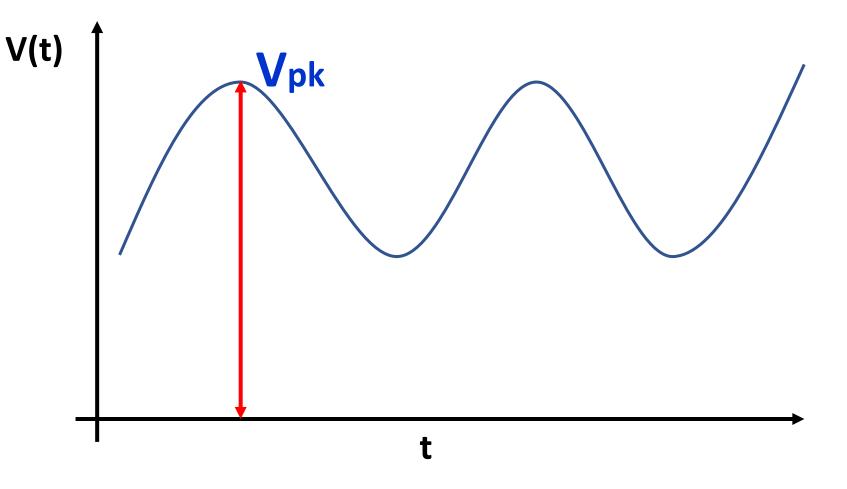
Lots of calculations!

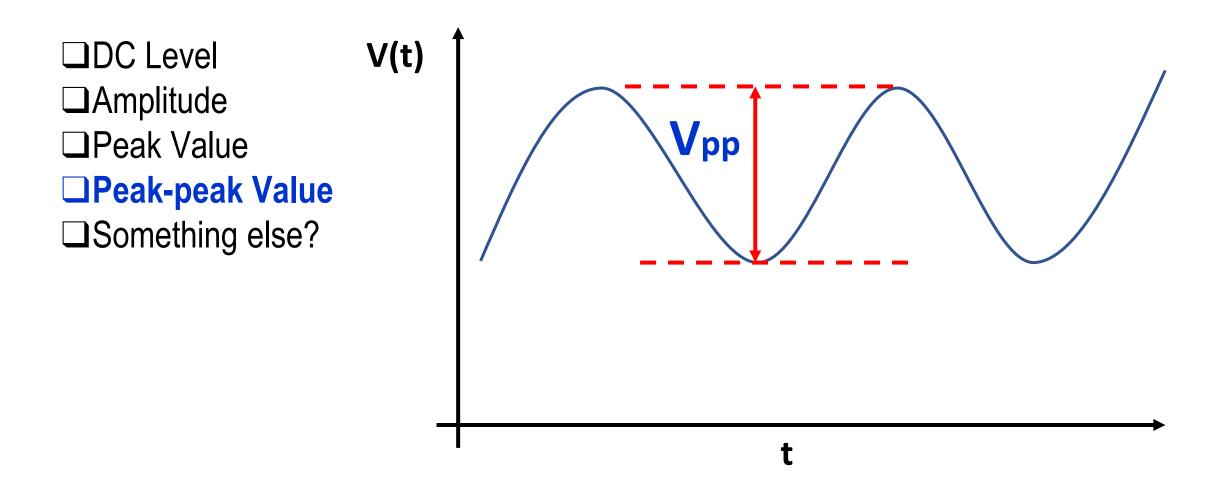


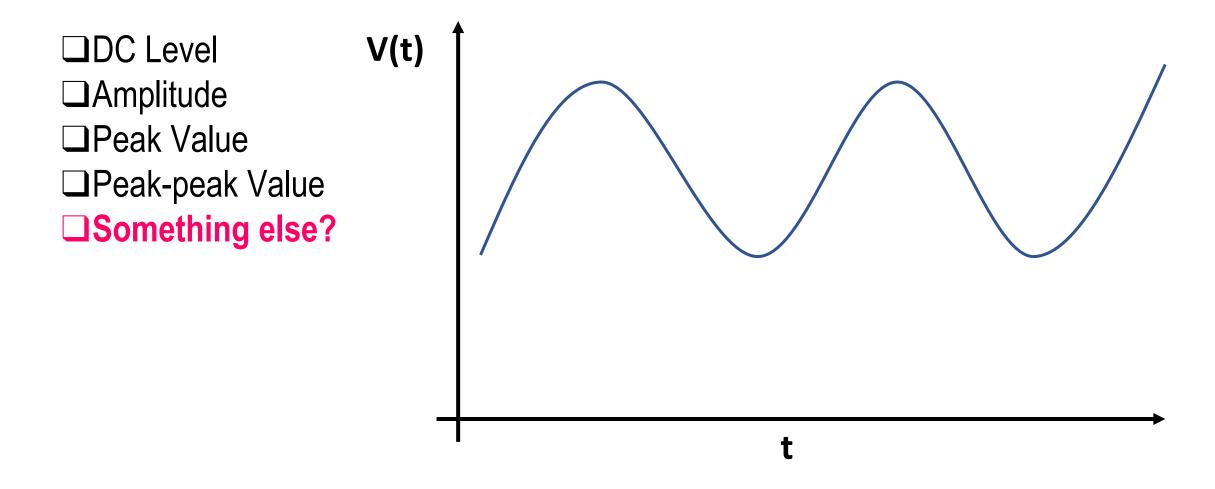




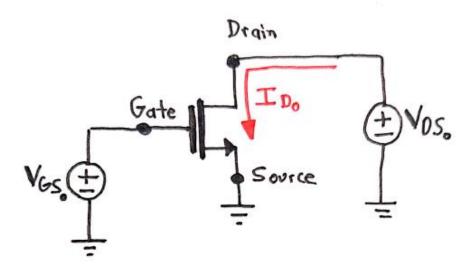
- □DC Level
- **□** Amplitude
- □Peak Value
- □Peak-peak Value
- ☐Something else?

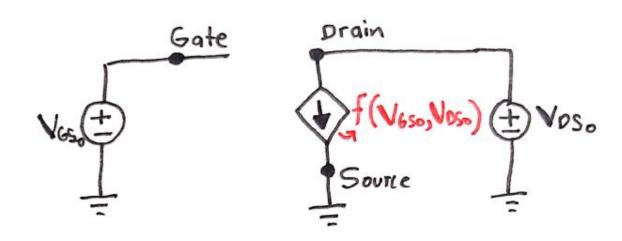






Bias Point





Bias Point

VGSO > VTH VGSO & VTH VDS. < VGS. - VTH

K'[(VGS. - VTH)VDS. - 1/2 VDS.)

TRIODE

VDS. > VGS. - VTH

1/2 K'(VGS. - VTH)

Or

1/2 K'(VGS. - VTH)

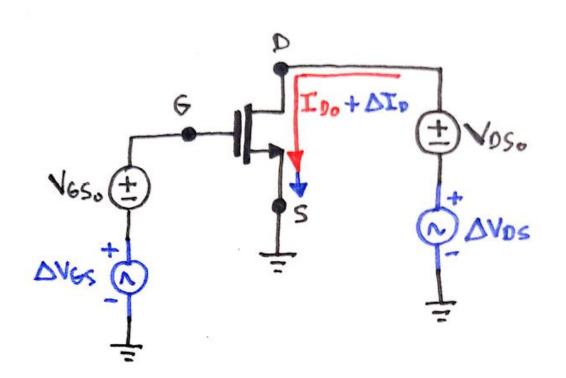
C.L.M

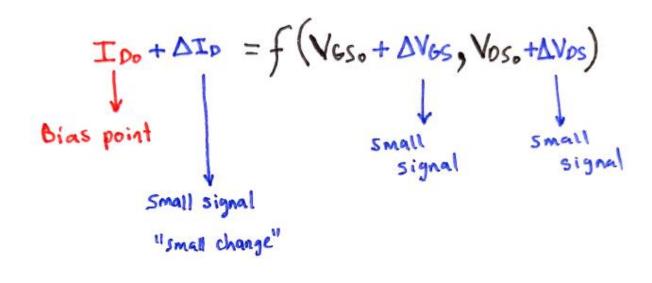
SATURATION

C.L.M $f(V_{GSO}, V_{DSO}) =$

$$\mathbf{K'} = \mu_n C_{ox} \frac{W}{L}$$

Changes around Bias





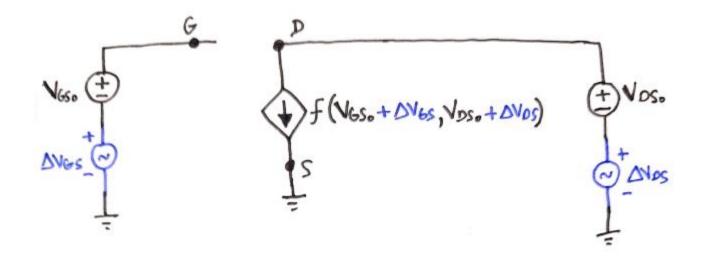
Changes around Bias

$$I_{Do} + \Delta I_{D} = f(V_{GSo}, V_{DSo}) + \frac{\partial f}{\partial V_{GS}} \cdot \Delta V_{GS} + \frac{\partial f}{\partial V_{DS}} \cdot \Delta V_{DS}$$

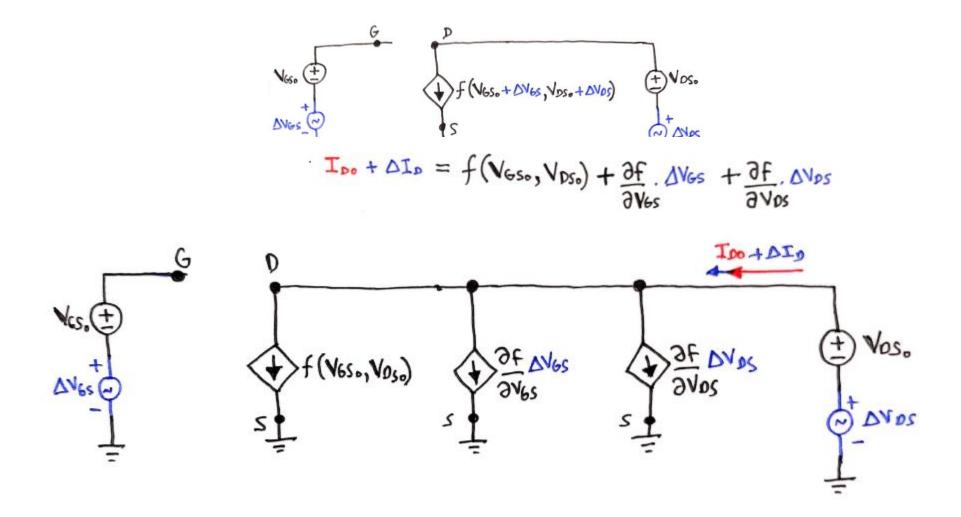
$$I_{Do} = f(V_{GSo}, V_{DSo}) \longrightarrow Bias point$$

$$\Delta I_{D} = \frac{\partial f}{\partial V_{GS}} \cdot \Delta V_{GS} + \frac{\partial f}{\partial V_{DS}} \cdot \Delta V_{DS} \longrightarrow small signal components$$

Circuit meaning



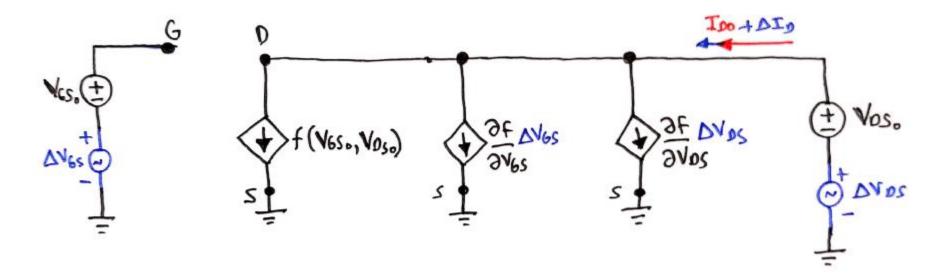
Circuit meaning: going to ss-model



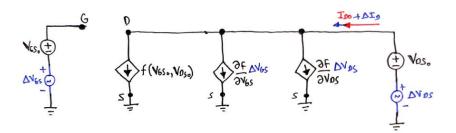
Circuit meaning going to ss-model

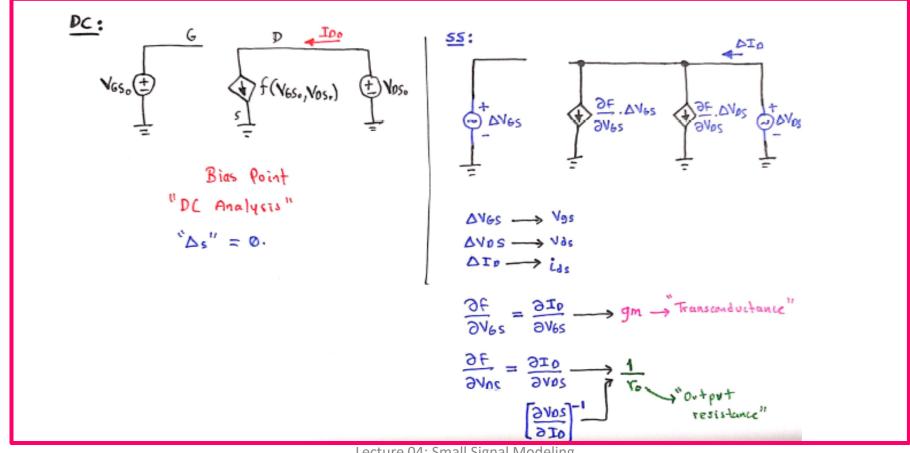
Current Law at D node

$$I_{D0} + \Delta I_D = f(V_{GS0}, V_{DS0}) + \frac{\partial f}{\partial V_{GS}} + \frac{\partial f}{\partial V_{DS}} + \frac{\partial f}{\partial V_{DS}}$$



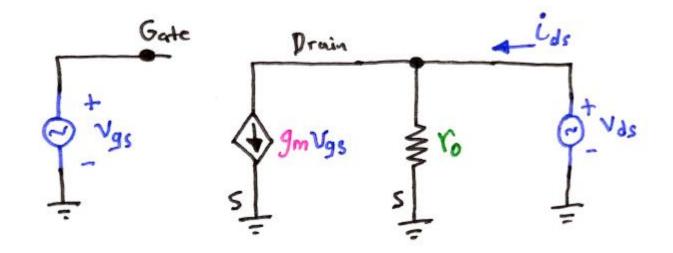
Circuit meaning going to ss-model





Small Signal Model (ss-model)

Low Frequency Small-Signal Model



Going to the details

$$I_{DS} = f(V_{GS}, V_{DS}, V_{BS})$$

$$\Delta I_{DS} = \frac{\partial I_{DS}}{\partial V_{GS}} \Delta V_{GS} + \frac{\partial I_{DS}}{\partial V_{DS}} \Delta V_{DS} + \frac{\partial I_{DS}}{\partial V_{BS}} \Delta V_{BS}$$

Going to the details

$$I_{DS} = f(V_{GS}, V_{DS}, V_{BS})$$

$$\Delta I_{DS} = \frac{\partial I_{DS}}{\partial V_{GS}} \Delta V_{GS} + \frac{\partial I_{DS}}{\partial V_{DS}} \Delta V_{DS} + \frac{\partial I_{DS}}{\partial V_{BS}} \Delta V_{BS}$$

Going to the details

$$I_{DS} = f(V_{GS}, V_{DS}, V_{BS})$$

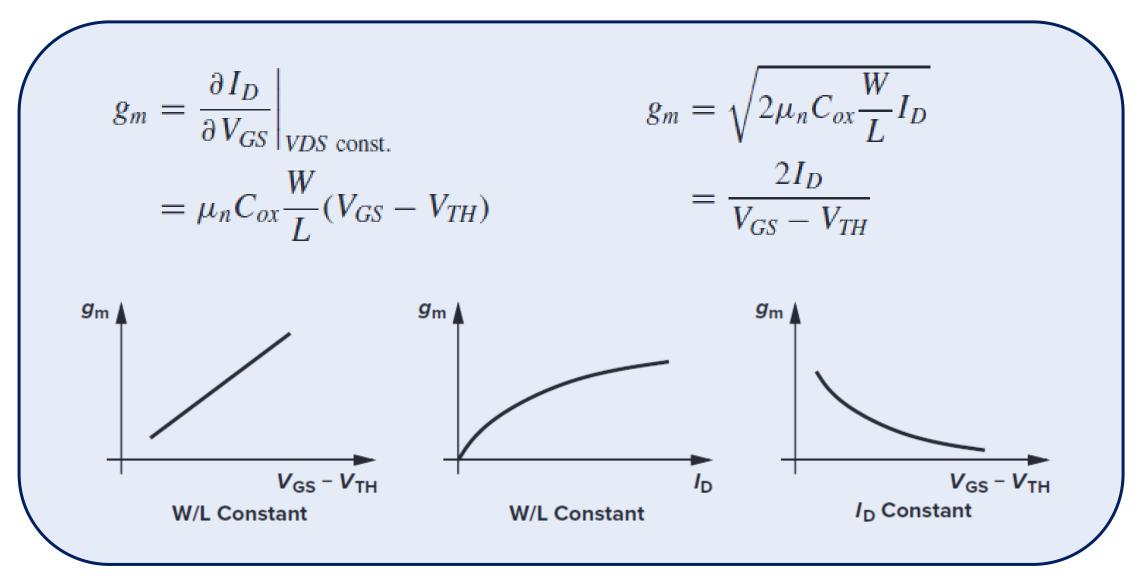
$$i_{ds} = \frac{\partial I_{DS}}{\partial V_{GS}} v_{gs} + \frac{\partial I_{DS}}{\partial V_{DS}} v_{ds} + \frac{\partial I_{DS}}{\partial V_{BS}} v_{bs}$$

$$i_{ds} = \frac{\partial I_{DS}}{\partial V_{GS}} v_{gs} + \frac{\partial I_{DS}}{\partial V_{DS}} v_{ds} + \frac{\partial I_{DS}}{\partial V_{RS}} v_{bs}$$

Transconductance

$$i_{ds} = \frac{\partial I_{DS}}{\partial V_{GS}} v_{gs} + \frac{\partial I_{DS}}{\partial V_{DS}} v_{ds} + \frac{\partial I_{DS}}{\partial V_{BS}} v_{bs}$$

$$g_m = \frac{\partial I_{DS}}{\partial V_{GS}}$$



$$g_{m} = \mu_{n}C_{ox}\frac{W}{L}(V_{GS} - V_{TH})(1 + \lambda V_{DS})$$

$$= \sqrt{2\mu_{n}C_{ox}(W/L)I_{D}(1 + \lambda V_{DS})}$$

$$= \frac{2I_{D}}{V_{GS} - V_{TH}}$$

$$g_{m}$$

$$V_{GS} - V_{TH}$$

$$W/L \text{ Constant}$$

$$W/L \text{ Constant}$$

$$W/L \text{ Constant}$$

$$g_{m}$$

$$V_{GS} - V_{TH}$$

$$i_{dS} = \frac{\partial I_{DS}}{\partial V_{GS}} v_{gS} + \frac{\partial I_{DS}}{\partial V_{DS}} v_{dS} + \frac{\partial I_{DS}}{\partial V_{BS}} v_{bS}$$

$$r_o = \left[\frac{\partial I_{DS}}{\partial V_{DS}}\right]^{-1}$$

MOSFET – Initial Thoughts

$$r_{O} = \frac{\partial V_{DS}}{\partial I_{D}}$$

$$= \frac{1}{\partial I_{D}/\partial V_{DS}}$$

$$= \frac{1}{\frac{1}{2}\mu_{n}C_{ox}\frac{W}{L}(V_{GS} - V_{TH})^{2} \cdot \lambda}$$

$$\approx \frac{1 + \lambda V_{DS}}{\lambda I_D}$$

$$\approx \frac{1}{\lambda I_D}$$

$$i_{dS} = \frac{\partial I_{DS}}{\partial V_{GS}} v_{gS} + \frac{\partial I_{DS}}{\partial V_{DS}} v_{dS} + \frac{\partial I_{DS}}{\partial V_{BS}} v_{bS}$$

$$g_{mb} = \frac{\partial I_{DS}}{\partial V_{BS}}$$

MOSFET – Initial Thoughts

$$g_{mb} = \frac{\partial I_D}{\partial V_{BS}}$$

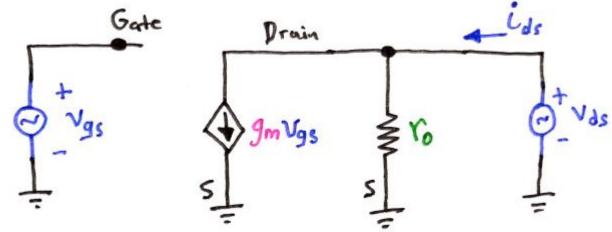
$$= \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH}) \left(-\frac{\partial V_{TH}}{\partial V_{BS}} \right)$$

$$\frac{\partial V_{TH}}{\partial V_{BS}} = -\frac{\partial V_{TH}}{\partial V_{SB}}$$
$$= -\frac{\gamma}{2} (2\Phi_F + V_{SB})^{-1/2}$$

$$g_{mb} = g_m \frac{\gamma}{2\sqrt{2\Phi_F + V_{SB}}}$$
$$= \eta g_m$$

Small-Signal Model Building

Something is missing \rightarrow ?



$$i_{ds} = g_m v_{gs} + \frac{1}{r_o} v_{ds} + g_{mb} v_{bs}$$

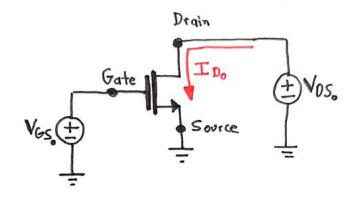
PMOS ss-model

$$i_{ds} = g_m v_{gs} + \frac{1}{r_o} v_{ds} + g_{mb} v_{bs}$$

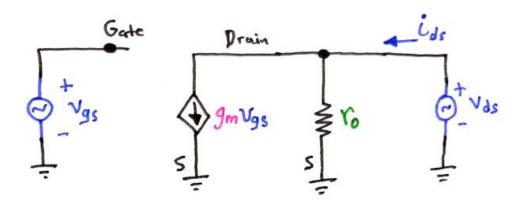
For a PMOS device it is easy to demonstrate that the ss-model is EXACTLY the same as in NMOS case IF and ONLY IF the same terminal labels and voltage references are used.

How to solve problems?

> DC analysis



➤ss Analysis



Let's solve our initial problem again!

Conclusions

- Note that the small signal model works on "Deltas" instead of the total voltage (or current) value.
- ➤ Small-signal model does not tell us anything about ABSOLUTE values!
- ➤ But it allow us to calculate the variations in a very useful way!
- ➤ We transform the MOSFET into a linear circuit!
- SS analysis is just one half of the work

Thanks

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